

Package (T _j =25 ; 0 - 100 °C) (FIG.7)	V _p	1	kV
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ELECTRICAL CHARACTERISTICS(T_j=25 °C)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	50	A
V _{GT}		- -	MAX.	1.3	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3k	- -	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	-	MAX.	80	A
				120	
I _H	I _T =1A		MAX.	70	A
dV/dt	V _D =1070V Gate Op n T _j =125		MIN.	1500	V/μs
(dV/dt) _C	(dV/dt) _C =20V/μs T _j =125		MIN.	28	A/μs
t ₀	I _G =80A I _A =400A I _R =40A T _j =25		TYP.	12	μs
t ₆				80	

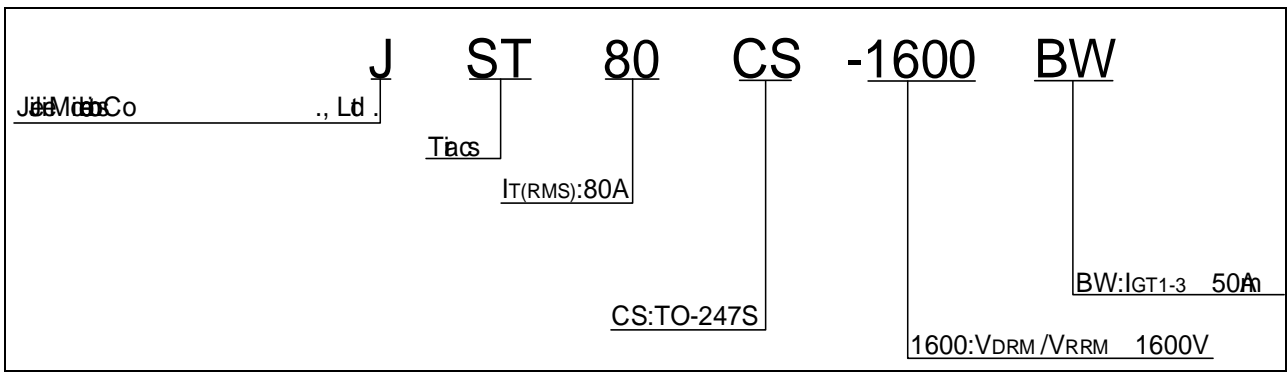
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =120A t _p =380μs	T _j =25	1.9	V
V _{TO}	T _{th}	T _j =125	0.71	V
R _D	D _{max}	T _j =125	23	m
I _{DRM}	V _D =V _{DRM} V _R =V _R RM	T _j =25	20	μA
I _{RRM}		T _j =125	12	A

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}			

ORDERING INFORMATION



MARKING

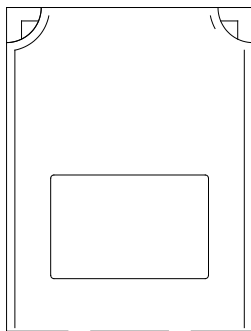


FIG.1: Main RMS
0 100



FIG.2: RMS 0 - 100
0 100

FIG.7

PACKAGE MECHANICAL DATA



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